Probing 10 kV and 100 A :

Challenges and Solutions for High Voltage / High Current Wafer Testing

Rainer Gaggl, Ph.D.

T.I.P.S. Messtechnik GmbH Villach, Austria office@tips.co.at

SWTW, June 2002



Overview

The D.U.T.: power semiconductors

- High voltage probing: effects going together with high voltage, solutions
- High current probecards: concepts, melting phenomena and causes
- Probe Tip Shape: T.I.P.S. "Probe Refresher"
- SmartClamp": protection of probes using active current limiting



The D.U.T.

MosFETs, IGBTs, Diodes with

- breakthrough voltages up to 6.5 kV
- forward currents up to 100 A



Power Diode, anode pad



IGBT, source and gate pads



High Voltage Testing (1)

 applied in probing breakthrough voltage of DUT
 challenges: sparking, flashovers on wafer surface and from probes to wafer



Damage on wafer surface (IGBT) due to flashover between source-pad and dicing frame structure



High Voltage Testing (2)

rule of thumb: for electrical field strength E > 2 kV/mm

flashovers may occur.



Fig. 2: high voltage test setup

E = U/d

- E ... field strenght
- U ... maximum test voltage

d ... minimum distance between high voltage pads



High Voltage Testing (3)

Theory: Physics of gas discharges

Flashover voltage as a function of gas pressure and electrodes distance is described in "Paschen" curves.



Fig. 3: Paschencurve for air [1]



Avoiding flashovers (1)

Chip design: avoid small pad distances

- + easy to test, feasible in some new designs
- not applicable for existing designs, chip area

Gas atmosphere with high dielectric strength (e.g. SF₆, CH₂Cl₂, CCl₄....) [2]

- + simple test setup
- gases are envrionmentally hazardous, very restricted use, expensive



Avoiding flashovers (2)

Testing in Liquid with high dielectric strength
 ? Wet testing process ?

High Vacuum: ionization length longer than critical dimensions on chip -> no gas discharge possible

? vacuum wafer test ?



"Luftpolster" concept

Compressed Air: breakthrough voltage in gases increase with gas pressure.

Basic idea: device is tested under compressed air





"Luftpolster" Probecard



2 kV / 100 A probecard with "Luftpolster" setup



High Current Testing

- Applied in probing forward voltage V_f of power diodes / on resistance R_{on} of IGBTs, MOSFETs
 challenges: thermal damage, melting of
 - probe tips, probe needles
 - bond pads beneath and around contact area







High Current Probecard (1)

current is distributed to multiple probes connected in parallel

ideal situation: contact and lead resistances are equal: currents are balanced



Electrical model of ideal high power probecard, 10 probes connected in parallel



High Current Probecard (2)

melting phenomena (probes, bond pad):

- due to excessive currents in single probes (> 15 A) much higher than the design current per probe
- cause: imbalanced currents in probes that arise from variations in contact resistance



Electrical model of real high power probecard, unequal contact resistances of probes



High Current Probecard (3)

Current distribution that might occur in a real high current probecard:





Probe Tip Shape (1)

"Passive" method: keep radius probe tip shape during lifetime of probecard for low contact resistance: "Probe Refresher": mechanical grinding of tip shape during probecard maintenance



flattened probe tip



... after grinding



Probe Tip Shape (2)





T.I.P.S. "Probe Refresher" machine



Probe Current Limiting (1)

"Active" method: "SmartClamp" - electronic circuitry in the lead to each probe individually limits current in each trace, has low resistance at nominal current





Probe Current Limiting (2)





"SmartClamp" module

Electrical characteristics of "SmartClamp" module

"SmartClamp" Probecard



100 A Probecard with 20 onboard SmartClamp modules







Infineon Technologies Austria AG Franz Reinwald et al.

References

[1] Der elektrische Durchschlag in Gasen, H.Hess, 1976[2] Hochspannungsisolierstoffe, A. Imhof, 1957

